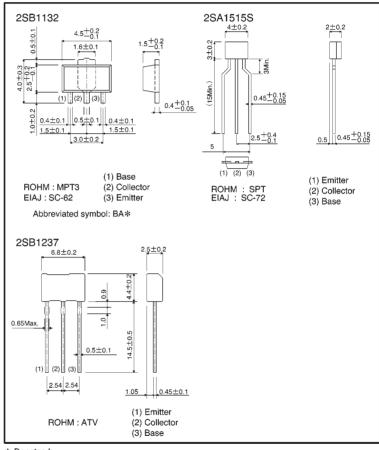
Medium Power Transistor (-32V, -1A)

2SB1132 / 2SA1515S / 2SB1237

● Features

- 1) Low $V_{CE(sat)}$. $V_{CE(sat)} = -0.2V \text{ (Typ.)}$ (Ic / IB = -500mA / -50mA)
- Compliments 2SD1664 / 2SD1858.
- ●Structure Epitaxial planar type PNP silicon transistor

External dimensions (Units: mm)



* Denotes her

●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		Vсво	-40	٧
Collector-emitter voltage		VCEO	-32	٧
Emitter-base voltage		VEBO	- 5	٧
Collector current		1-	-1	A (DC)
		lc	-2	A (Pulse) *1
Collector power dissipation	2SB1132		0.5	
			2	*2 W
	2SA1515S	Pc	0.3	VV
	2SB1237		1	*3
Junction temperature		Tj	150	င
Storage temperature		Tstg	-55~ + 150	°C

^{*1} Single pulse, Pw=100ms

●Electrical characteristics (Ta = 25°C)

Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage		ВУсво	-40	_	_	٧	Ic=-50 μ A	
Collector-emitter breakdown voltage		BVceo	-32	_	_	V	Ic=-1mA	
Emitter-base breakdown voltage		ВУЕВО	- 5	_	_	V	I _E =-50 μ A	
Collector cutoff current		Ісво	_	_	-0.5	μΑ	V _{CB} =-20V	
Emitter cutoff current		Ієво	_	_	-0.5	μΑ	V _{EB} =-4V	
Collector-emitter saturation voltage		VCE(sat)	_	-0.2	-0.5	٧	Ic/I _B =-500mA/-50mA *	
DC current transfer ratio	2SB1132, 2SB1237		82	_	390	_	3	
	2SA1515S	hfE	120	_	390	_	VcE=-3V, Ic=-0.1A	
Transition frequency		fτ	_	150	_	MHz	VcE=-5V, IE=50mA, f=30MHz	
Output capacitance		Cob	_	20	30	pF	V _{CB} =-10V, I _E =0A, f=1MHz	

 $[\]boldsymbol{*}$ Measured using pulse current.

●Packaging specifications and hFE

		Package	Taping		
		Code	T100	TP	TU2
Type	hfE	Basic ordering unit (pieces)	1000	5000	2500
2SB1132	PQR		0	_	_
2SA1515S	QR		_	0	_
2SB1237	PQR		_	_	0

hFE values are classified as follows:

Item	Р	Q	R
hre	82~180	120~270	180~390

^{*2} When mounted on a 40×40×0.7 mm ceramic board.

^{*3} Printed circuit board, 1.7 mm thick, collector copper plating 100mm² or larger.

Electrical characteristic curves

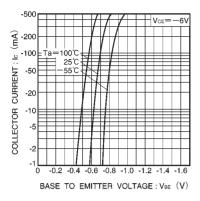


Fig.1 Grounded emitter propagation characteristics

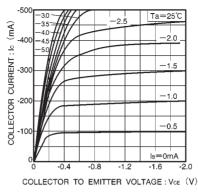


Fig.2 Grounded emitter output characteristics

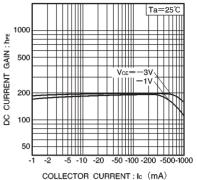


Fig.3 DC current gain vs.

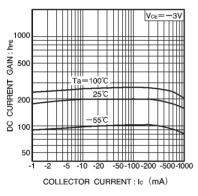


Fig.4 DC current gain vs. collector current (II)

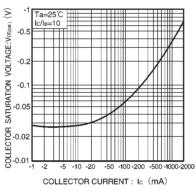


Fig.5 Collector-emitter saturation voltage vs. collector current

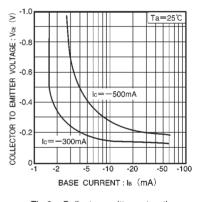


Fig.6 Collector-emitter saturation voltage vs. base current

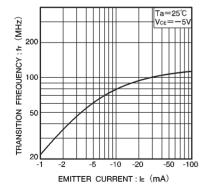


Fig.7 Gain bandwidth product vs. emitter current

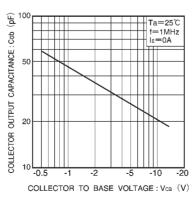


Fig.8 Collector output capacitance vs. collector-base voltage

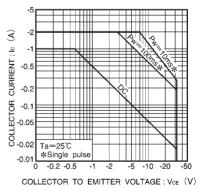
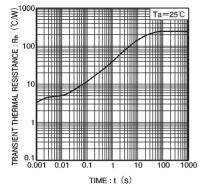
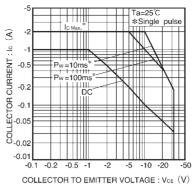


Fig.9 Safe operation area (2SB1132)





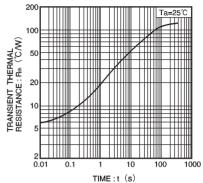


Fig.10 Transient thermal resistance (2SB1132)

Fig.11 Safe operation area (2SB1237)

Fig.12 Transient thermal resistance (2SB1237)

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2N2369ADCSM 2N5769 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E
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